



# FQD1N60C / FQU1N60C

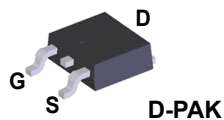
## N-Channel QFET<sup>®</sup> MOSFET 600 V, 1.0 A, 11.5 Ω

### Features

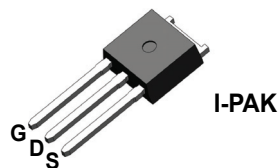
- 1 A, 600 V,  $R_{DS(on)} = 11.5 \Omega$  (Max.) @  $V_{GS} = 10$  V,  $I_D = 0.5$  A
- Low Gate Charge (Typ. 4.8 nC)
- Low Crss (Typ. 3.5 pF)
- 100% Avalanche Tested
- RoHS Compliant

### Description

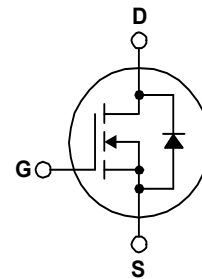
This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.



D-PAK



I-PAK



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQD1N60CTM / FQU1N60CTU	Unit
$V_{DSS}$	Drain-Source Voltage	600	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	1	A
		0.6	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	4	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	33	mJ
$I_{AR}$	Avalanche Current (Note 1)	1	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	2.8	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ (Note 3)	4.5	V/ns
$P_D$	Power Dissipation ( $T_A = 25^\circ\text{C}$ )*	2.5	W
	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	28	W
	- Derate Above $25^\circ\text{C}$	0.22	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FQD1N60CTM / FQU1N60CTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	4.53	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Minimum Pad of 2-oz Copper), Max.	110	
	Thermal Resistance, Junction-to-Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50	

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD1N60CTM	FQD1N60C	D-PAK	Tape and Reel	330 mm	16mm	2500 units
FQU1N60CTU	FQU1N60C	I-PAK	Tube	N/A	N/A	70 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	600	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.6	--	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.5\text{ A}$	--	9.3	11.5	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 0.5\text{ A}$	--	0.75	--	S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	130	170	pF
$C_{oss}$	Output Capacitance		--	19	25	pF
$C_{riss}$	Reverse Transfer Capacitance		--	3.5	4.5	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 1.1\text{ A},$ $R_G = 25\ \Omega$	--	7	24	ns
$t_r$	Turn-On Rise Time		--	21	52	ns
$t_{d(off)}$	Turn-Off Delay Time		--	13	36	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	27	64
$Q_g$	Total Gate Charge	$V_{DS} = 480\text{ V}, I_D = 1.1\text{ A},$ $V_{GS} = 10\text{ V}$	--	4.8	6.2	nC
$Q_{gs}$	Gate-Source Charge		--	0.7	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	2.7	--
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	1	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	4	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.5\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 1.1\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	190	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	0.53	--	$\mu\text{C}$

### Notes:

1. Repetitive Rating : pulse-width limited by maximum junction temperature.
2.  $L = 59\text{ mH}, I_{AS} = 1.1\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 1.1\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

## Typical Characteristics

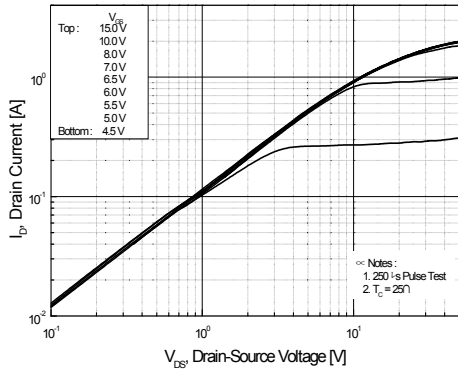


Figure 1. On-Region Characteristics

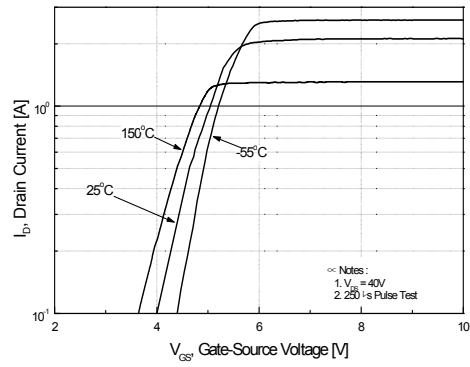


Figure 2. Transfer Characteristics

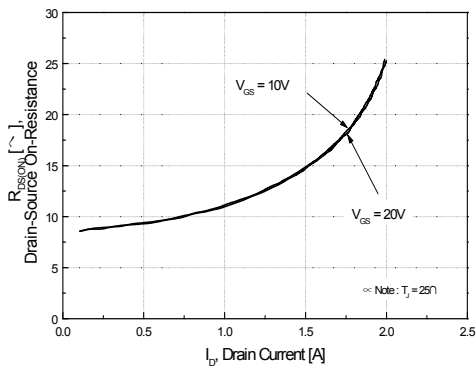


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

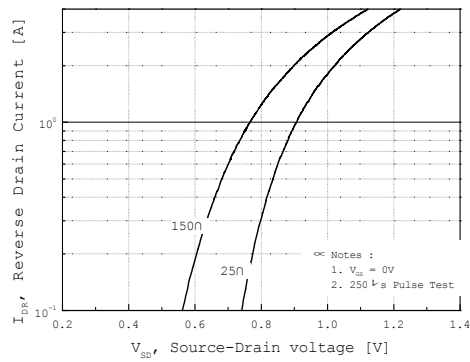


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

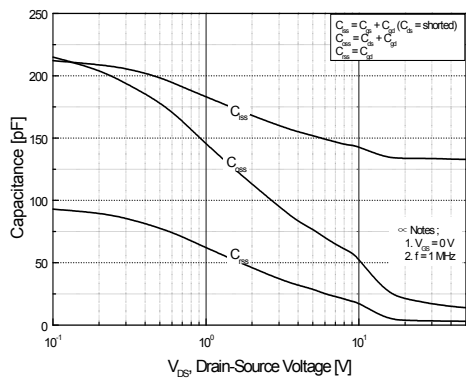


Figure 5. Capacitance Characteristics

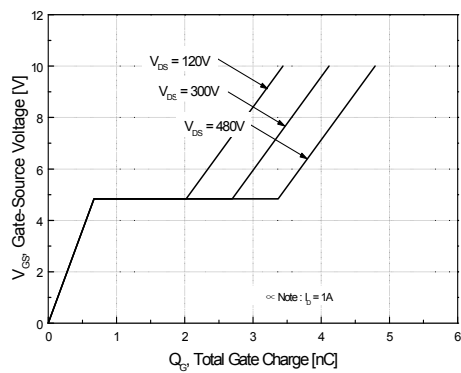
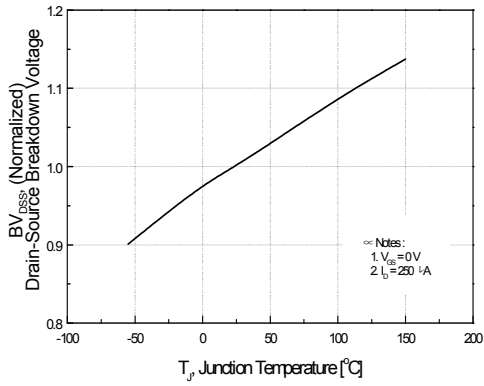
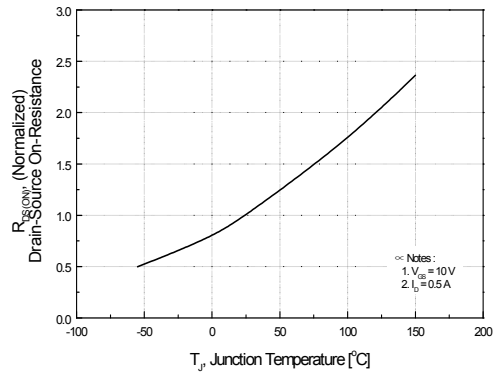


Figure 6. Gate Charge Characteristics

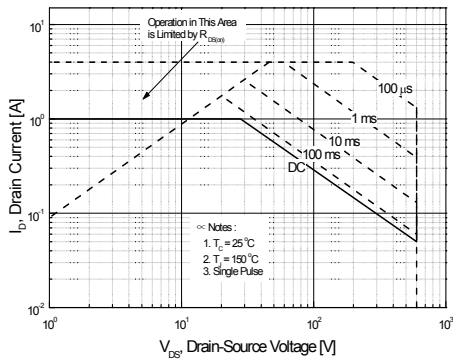
**Typical Characteristics** (Continued)



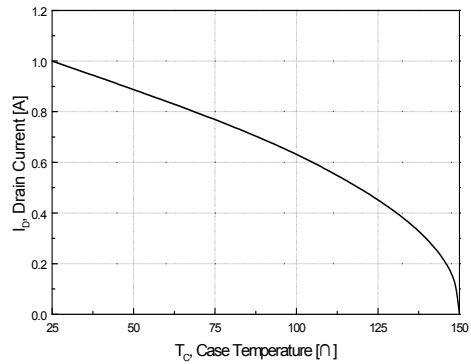
**Figure 7. Breakdown Voltage Variation vs Temperature**



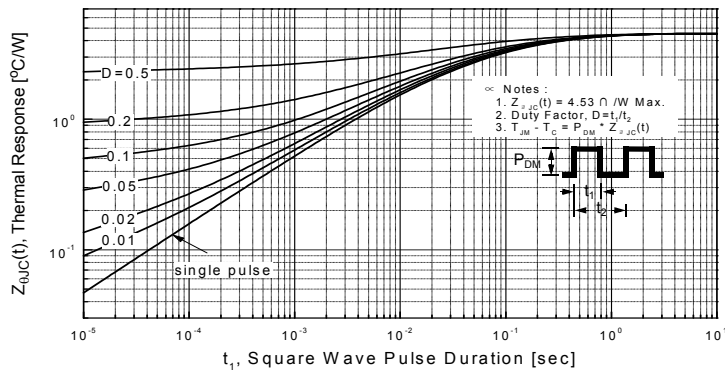
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9. Maximum Safe Operating Area**

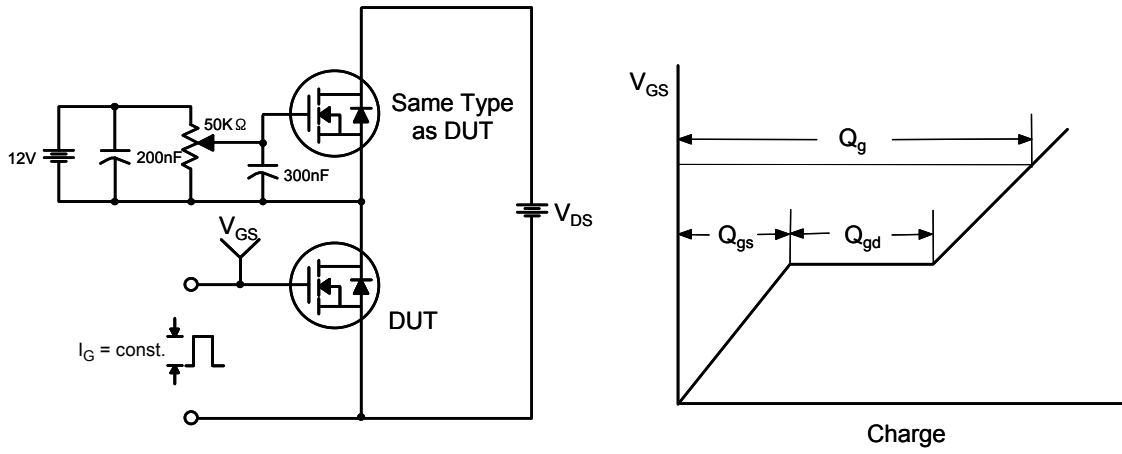


**Figure 10. Maximum Drain Current vs Case Temperature**

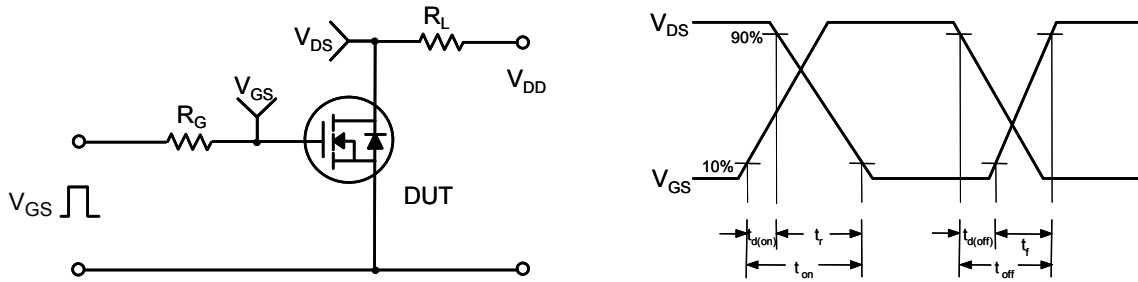


**Figure 11. Transient Thermal Response Curve**

**Figure 12. Gate Charge Test Circuit & Waveform**



**Figure 13. Resistive Switching Test Circuit & Waveforms**



**Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms**

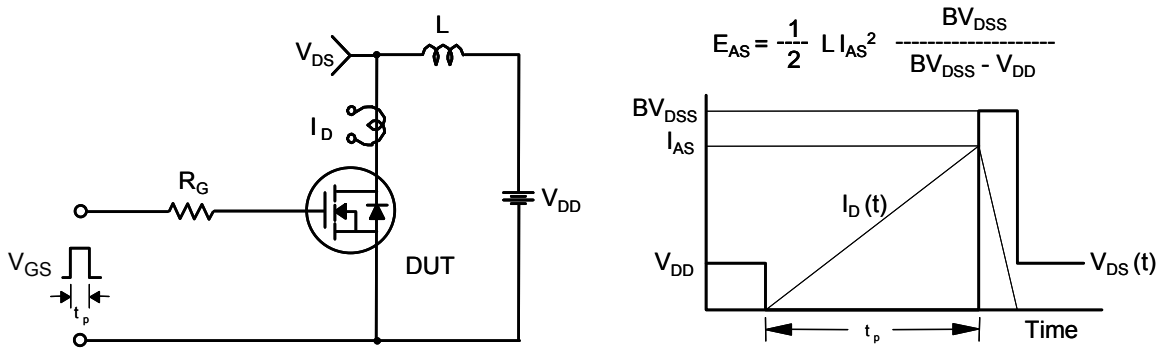
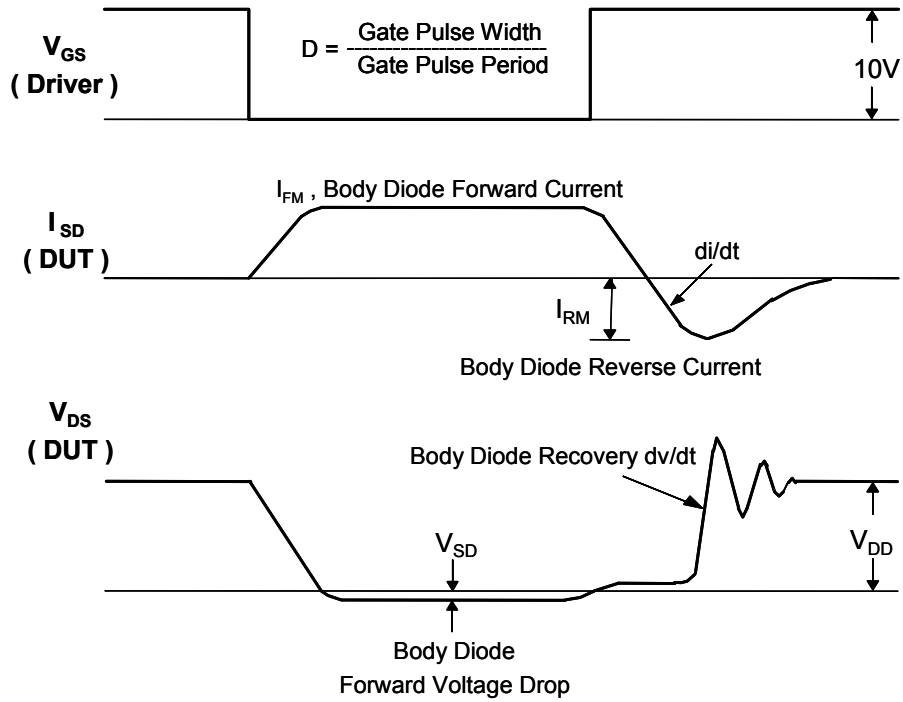
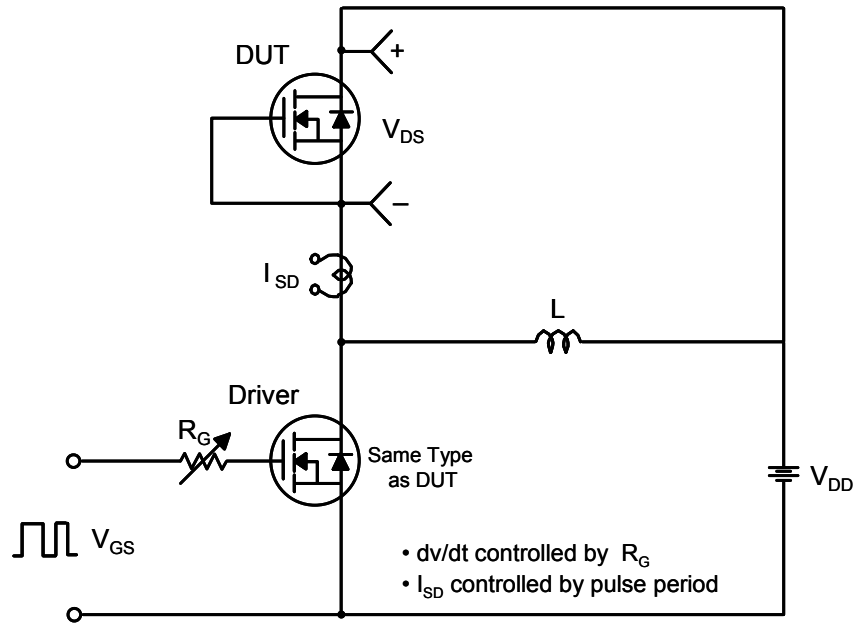


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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